Piezoelectric properties of Ga$_2$O$_3$: a first-principle study

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The compounds exhibit piezoelectricity, which demands to break inversion symmetry, and then to be a semiconductor. For Ga$_2$O$_3$, the orthorhombic case (ε-Ga$_2$O$_3$) of common five phases breaks inversion symmetry. Here, the piezoelectric tensor of ε-Ga$_2$O$_3$ is reported by using density functional perturbation theory (DFPT). To confirm semiconducting properties of ε-Ga$_2$O$_3$, its electronic structures are studied by using generalized gradient approximation (GGA) and Tran and Blaha’s modified Becke and Johnson (mBJ) exchange potential. The gap value of 4.66 eV is predicted with mBJ method, along with the the effective mass tensor for electrons at the conduction band minimum (CBM) [about 0.24 m$_0$]. The mBJ gap is very close to the available experimental value. The elastic tensor $C_{ij}$ and piezoelectric stress tensor $e_{ij}$ are attained by DFPT, and then piezoelectric strain tensor $d_{ij}$ are calculated from $C_{ij}$ and $e_{ij}$. In this process, average mechanical properties of ε-Ga$_2$O$_3$ are estimated, such as bulk modulus, Shear modulus, Young’s modulus and so on. The calculated $d_{ij}$ are comparable and even higher than commonly used piezoelectric materials such as α-quartz, ZnO, AlN and GaN.

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I. INTRODUCTION

Wide-band gap semiconductors have potential application in high-power electronics, which requires high frequency, temperature and power. Gallium oxide (Ga$_2$O$_3$) has received a lot of attention as a wide band gap transparent semiconducting oxide$^{1-6}$. The Ga$_2$O$_3$ has five different phases, commonly referred to as α, β, γ, δ and ε, the monoclinic β phase of which is the most thermodynamically stable with the energy gap 4.6-4.9 eV, transparency up to the UV-C range, and very high breakdown voltage$^{1,3}$. Piezoelectric materials can convert mechanical energy to electrical energy, which have potential application in sensors and energy harvesting$^7$. The ZnO, GaN and InN semiconductors with non-centrosymmetric wurtzite-structure are wildly used in the piezotronic and piezo-phototronic devices, and their nanostructures have potential applications in electromechanical coupled sensors and nanoscale energy conversion$^8-11$.

For piezoelectric materials, inversion symmetry need be eliminated. The bravais lattice, space group, point group and inversion center of five different polymorphs of Ga$_2$O$_3$ are shown in Table I. It is clearly seen that ε-Ga$_2$O$_3$ breaks inversion symmetry and hence can exhibit piezoelectricity. The ε-phase of Ga$_2$O$_3$ is confirmed as the second most stable structure after β-Ga$_2$O$_3$.$^{12}$ When ε-Ga$_2$O$_3$ is epitaxially stabilized, the symmetry will prevent the transform back into β-phase. The electronic structures of ε-Ga$_2$O$_3$ have been reported, and the predicted gap is 2.465 eV with GGA$^{13}$, 2.32 eV with PBEsol, 4.62 eV with B3LYP$^{14}$ and 4.26 eV with HSE$^{15}$. The experimental gap is 4.41 eV by angle-resolved photoemission spectroscopy (ARPES) experiments$^{15}$, and is 4.6 eV from photoconductivity and optical absorption$^{16}$. The ε-Ga$_2$O$_3$ is predicted to have a large spontaneous polarization (0.23-0.26 C/m$^2$)$^{12,14}$, along with piezoelectric coefficient $e_{33}=0.77$ C/m$^{12}$. Recently, piezoelectric strain constants ($d_{ij}$) of ε-Ga$_2$O$_3$ are calculated from piezoelectric stress constants ($e_{ij}$) and elastic constants ($C_{ij}$)$^{15,16}$. The $e_{ij}$ are attained by polarization-strain relation, and the $C_{ij}$ are calculated by energy-stain relation$^{17}$. Here, we use DFTP to attain the $C_{ij}$ and $e_{ij}$, and then calculate the $d_{ij}$ by $e$ matrix multiplying $C$ matrix inversion.

To ensure the reliability of our results, the piezoelectric properties of commonly used piezoelectric materials such as ZnO, AlN and GaN are also studied by DFTP, and make a comparison with the related experiments$^{18-22}$. The mBJ is used to study the electronic structures of ε-Ga$_2$O$_3$, and the calculated mBJ gap 4.66 eV is very close to experimental values$^{15,16}$. The mBJ is as cheap as local density approximation (LDA) or GGA, thus can be used to study very large systems such as doping ε-Ga$_2$O$_3$ in an efficient way.

II. SYMMETRY ANALYSIS

The piezoelectric effect is an electromechanical coupling described by piezoelectric tensors $e_{ijk}$ and $d_{ijk}$, which are obtained as the sum of ionic and electronic contributions. In the following, the frequently used Voigt notation is employed, and the mapping of indices is 11→1, 22→2, 33→3, 23→4, 31→5 and 12→6. The Voigt notation allows to represent the tensor of elastic constants.
$C_{ijkl}$, piezoelectric tensors $e_{ijk}$ and $d_{ijk}$ as $6 \times 6, 3 \times 6$ and $3 \times 6$ matrix $C_{ij}$, $e_{ij}$ and $d_{ij}$, with a maximum of 21, 18 and 18 independent elements. The number of independent components can be reduced due to the crystal symmetry in $C_{ij}$, $e_{ij}$ and $d_{ij}$ tensors. The $\epsilon$-Ga$_2$O$_3$ has the $mm2$ point group symmetry, giving:

$$
e = 
\begin{pmatrix}
0 & 0 & 0 & 0 & e_{15} & 0 \\
0 & 0 & 0 & e_{24} & 0 & 0 \\
e_{31} & e_{32} & e_{33} & 0 & 0 & 0
\end{pmatrix}
$$

(1)

$$
C = 
\begin{pmatrix}
C_{11} & C_{12} & C_{13} & 0 & 0 & 0 \\
C_{12} & C_{22} & C_{23} & 0 & 0 & 0 \\
C_{13} & C_{23} & C_{33} & 0 & 0 & 0 \\
0 & 0 & 0 & C_{44} & 0 & 0 \\
0 & 0 & 0 & 0 & C_{55} & 0 \\
0 & 0 & 0 & 0 & 0 & C_{66}
\end{pmatrix}
$$

(2)

The elastic tensor $C_{ij}$ and piezoelectric stress tensor $e_{ij}$ can be attained by density functional theory (DFT) calculations, and the piezoelectric strain tensor $d_{ij}$ can be calculated by the relation:

$$
e = dC
$$

(3)

and

$$
d = 
\begin{pmatrix}
0 & 0 & 0 & 0 & d_{15} & 0 \\
0 & 0 & 0 & d_{24} & 0 & 0 \\
d_{31} & d_{32} & d_{33} & 0 & 0 & 0
\end{pmatrix}
$$

(4)

### III. ELECTRONIC STRUCTURES

The crystal structure of $\epsilon$-Ga$_2$O$_3$ has 16 (24) Ga (O) atoms at four (six) different Wyckoff positions 4a, which is plotted in Figure 1. Within the DFT, a full-potential linearized augmented-plane-waves method is used to investigate electronic structures of Ga$_2$O$_3$ by using WIEN2k code. We use Tran and Blaha’s mBJ approach for the exchange potential (plus LDA correlation potential), and the popular GGA of Perdew, Burke and Ernzerhof (GGA-PBE) to do comparative studies. We use a $12 \times 7 \times 6$ k-point meshes in the first Brillouin zone (BZ) for the self-consistent calculation, make harmonic expansion up to $l_{\text{max}} = 10$ in each of the atomic spheres, and set $R_{\text{mt}} \cdot k_{\text{max}} = 8$.

The optimized structure-related data are summarized in Table II by using GGA, which agree well with previous calculated values. Firstly, the popular GGA is used to perform the self-consistent calculation, and the improved exchange-correlation functional including the mBJ exchange potential is adopted, which can improve the semiconductor gaps and d state positions for many kinds of materials. The energy bands calculated with GGA and mBJ are presented in Figure 2. The GGA gap value is 2.45 eV, and 4.66 eV for mBJ functional. Our GGA gap accords with other GGA value 2.465 eV. The mBJ gap is very close to HSE one (4.26 eV) and B3LYP one (4.62 eV), and is also close to experimental value 4.41 eV by ARPES experiments and 4.6 eV indicated by photoconductivity and optical absorption. Both GGA and mBJ results show a CBM at the G point. A quasidirect gap is observed with the valence band maximum (VBM) is a bit off G in the G-X direction. The energy difference between G point and VBM only is 1.2 meV with GGA and 0.2 meV with mBJ. The experimental data suggest that the VBM is at or near the zone centre. The experimental gap for $\beta$-Ga$_2$O$_3$ has been reported in the range of 4.6-4.9 eV. The mBJ is used to study the electronic structures of $\beta$-Ga$_2$O$_3$ (a=12.29 Å, b=3.05 Å, c=5.81 Å and $\beta$=103.77). The mBJ gap value of $\beta$-Ga$_2$O$_3$ is 4.61 eV, which shows that mBJ can reproduce the gap of Ga$_2$O$_3$ very well. We also determine the effective mass tensor for electrons at the CBM, and the resulting results in units of the free electron mass $m_0$ are: $m_{xx} = 0.237$, and $m_{yy}=m_{zz}=0.235$, which shows that

<table>
<thead>
<tr>
<th>atom</th>
<th>x</th>
<th>y</th>
<th>z</th>
</tr>
</thead>
<tbody>
<tr>
<td>Ga1</td>
<td>0.18017</td>
<td>0.15153</td>
<td>0.99762</td>
</tr>
<tr>
<td>Ga2</td>
<td>0.81334</td>
<td>0.16181</td>
<td>0.30879</td>
</tr>
<tr>
<td>Ga3</td>
<td>0.19165</td>
<td>0.15083</td>
<td>0.58692</td>
</tr>
<tr>
<td>Ga4</td>
<td>0.67799</td>
<td>0.03128</td>
<td>0.79570</td>
</tr>
<tr>
<td>O1</td>
<td>0.97429</td>
<td>0.32590</td>
<td>0.42764</td>
</tr>
<tr>
<td>O2</td>
<td>0.52161</td>
<td>0.48778</td>
<td>0.43308</td>
</tr>
<tr>
<td>O3</td>
<td>0.65030</td>
<td>0.00345</td>
<td>0.20151</td>
</tr>
<tr>
<td>O4</td>
<td>0.15460</td>
<td>0.15917</td>
<td>0.19757</td>
</tr>
<tr>
<td>O5</td>
<td>0.84997</td>
<td>0.17145</td>
<td>0.67252</td>
</tr>
<tr>
<td>O6</td>
<td>0.52301</td>
<td>0.16682</td>
<td>0.93836</td>
</tr>
</tbody>
</table>
FIG. 2. The energy band structures of $\epsilon$-Ga$_2$O$_3$ using GGA (Left) and mBJ (Right).

<table>
<thead>
<tr>
<th>$B$ (GPa)</th>
<th>$G$ (GPa)</th>
<th>$E$ (GPa)</th>
<th>$\nu$</th>
</tr>
</thead>
<tbody>
<tr>
<td>209.22</td>
<td>82.50</td>
<td>218.75</td>
<td>0.33</td>
</tr>
</tbody>
</table>

<table>
<thead>
<tr>
<th>$v_l$ (km/s)</th>
<th>$v_t$ (km/s)</th>
<th>$v_a$ (km/s)</th>
<th>$\Theta_D$ (K)</th>
</tr>
</thead>
<tbody>
<tr>
<td>7.24</td>
<td>3.68</td>
<td>4.12</td>
<td>565.81</td>
</tr>
</tbody>
</table>

Based on $C_{ij}$, average mechanical properties of $\epsilon$-Ga$_2$O$_3$ can be attained, including bulk modulus, shear modulus, Young’s modulus, Poisson’s ratio, longitudinal wave velocity, transverse wave velocity, average wave velocity and Debye temperature. The Born criteria of mechanical stability for an orthorhombic crystal is:

$$C_{11} > 0, C_{44} > 0, C_{55} > 0, C_{66} > 0 \quad (6)$$

$$C_{11}C_{22} > C_{12}^2 \quad (7)$$

$$C_{11}C_{22}C_{33} + 2C_{12}C_{13}C_{23} - C_{11}C_{23}^2 - C_{22}C_{13}^2 - C_{33}C_{12}^2 > 0 \quad (8)$$

The calculated $C_{ij}$ satisfy these conditions, proving that $\epsilon$-Ga$_2$O$_3$ is mechanically stable. The related data are summarized in Table III. The bulk (shear) modulus $B$ ($G$) manifests the resistance to fracture (plastic deformation). A high (low) $B/G$ ratio may indicates its
TABLE V. Piezoelectric coefficients $e_{ij}(d_{ij})$ of ZnO, AlN and GaN, and the unit is C/m$^2$ (pm/V). The related experimental values of ZnO$^{18}$, AlN$^{19}$ and GaN$^{19-22}$ are shown in parentheses.

<table>
<thead>
<tr>
<th>Name</th>
<th>$e_{33}$</th>
<th>$e_{31}$</th>
<th>$e_{15}$</th>
<th>$d_{33}$</th>
<th>$d_{31}$</th>
<th>$d_{15}$</th>
</tr>
</thead>
<tbody>
<tr>
<td>ZnO</td>
<td>1.33 (0.96)</td>
<td>-0.65 (-0.62)</td>
<td>-0.49 (-0.37)</td>
<td>13.63 (12.3)</td>
<td>-6.59 (-5.1)</td>
<td>-14.20 (-8.3)</td>
</tr>
<tr>
<td>AlN</td>
<td>1.61 (1.55)</td>
<td>-0.65 (-0.58)</td>
<td>-0.34 (-0.48)</td>
<td>5.65 (5.53)</td>
<td>-2.34 (-2.65)</td>
<td>-3.00 (-4.07)</td>
</tr>
<tr>
<td>GaN</td>
<td>0.67 (1.06$^{19}$)</td>
<td>-0.37 (-0.36$^{19}$)</td>
<td>-0.23 (-0.30$^{19}$)</td>
<td>2.38 (3.1$^{20}$)</td>
<td>-1.24 (-1.0$^{21}$)</td>
<td>-2.52 (-3.1$^{22}$)</td>
</tr>
</tbody>
</table>

ductility (brittleness), and the critical value is around 1.75, which can be used to separate ductile and brittle materials. The value of $\epsilon$-Ga$_2$O$_3$ is 2.54, and it can be classified as a ductility material.

The piezoelectric stress tensor $e_{ij}$ are shown (in C/m$^2$):

$$
\begin{pmatrix}
0 & 0 & 0 & 0 & 0.595 & 0 \\
0 & 0 & 0 & 0.194 & 0 & 0 \\
0.011 & -0.319 & 0.941 & 0 & 0 & 0
\end{pmatrix}
$$

The piezoelectric strain tensor $d_{ij}$ are derived by Equation 3, giving (in pm/V):

$$
\begin{pmatrix}
0 & 0 & 0 & 0 & 9.622 & 0 \\
0 & 0 & 0 & 0 & 0 & 2.345 \\
-0.489 & -3.060 & 4.858 & 0 & 0 & 0
\end{pmatrix}
$$

The $\epsilon$-Ga$_2$O$_3$ possesses five independent components of the piezoelectric tensor, namely $d_{31}$, $d_{32}$, $d_{33}$, $d_{15}$ and $d_{24}$. The magnitudes of $d_{ij}$ range from 0.489 pm/V to 9.622 pm/V, the $d_{33}$ and $d_{15}$ of which are comparable and even higher than commonly used piezoelectric materials such as $\alpha$-quartz, ZnO, AlN and GaN$^{18-22}$. We note that $d_{33}$ is smaller by 1 order of magnitude compared to other $d_{ij}$, which is due to very small $e_{31}$. The $d_{15}$ is the largest among the $d_{ij}$, which is due to the large $e_{15}$ and the smallest $C_{55}$ ($d_{15}=e_{15}/C_{55}$). Our calculated $d_{15}$ are close to previous theoretical values ($d_{33}=-3.43$ pm/V, $d_{31}=4.06$ pm/V, $d_{24}=2.69$ pm/V, $d_{15}=14.60$ pm/V) except $d_{31}$ (1.37 pm/V)$^{17}$. In previous calculations, the elastic tensor $C_{ij}$ are attained by fitting the DFT-calculated unit-cell energy to a series of strain states, and the piezoelectric stress tensor $e_{ij}$ are calculated by evaluating the change of unit-cell polarization after imposing small strain$^{17}$. Here, these tensors are calculated by DFPT. To ensure the reliability of our results or method, the piezoelectric properties of ZnO, AlN and GaN with $P6_3mc$ space group are also studied by DFPT. Due to $6mm$ point group of $P6_3mc$, they have five independent elastic constants ($C_{11}, C_{12}, C_{13}, C_{33}$ and $C_{44}$), and three piezoelectric constants ($\epsilon/e_{31}, \epsilon/d_{33}$ and $\epsilon/d_{15}$). The elastic constants of ZnO, AlN and GaN are shown in Table IV, which agree well with previous calculated values$^{33}$. The piezoelectric tensors of ZnO, AlN and GaN are summarized in Table V, along with the related experimental values of ZnO$^{18}$, AlN$^{19}$ and GaN$^{19-22}$. Our calculated piezoelectric tensors of ZnO, AlN and GaN are in reasonable agreement with experiments. The deviation may be because the related experiments are carried out on constrained epitaxial samples. Thus, our predicted piezoelectric tensors of $\epsilon$-Ga$_2$O$_3$ should be receivable.

V. DISCUSSIONS AND CONCLUSION

It is clear that mBJ gives much better energy gap of $\epsilon$-Ga$_2$O$_3$ than GGA toward the experimental values. Although HSE or B3LYP also can give reasonable energy gap, they need more CPU time and memory than mBJ. Thus, mBJ may be more suitable for dopant studies of $\epsilon$-Ga$_2$O$_3$. It is noted that the energy gap and the effective masses (at CBM) of $\epsilon$-Ga$_2$O$_3$ are very close to ones of $\beta$ case, but $\epsilon$ phase shows good piezoelectric properties, which can add more freedom for electronic devices.

In summary, the electronic structures have been studied by GGA and mBJ, and the elastic and piezoelectric tensors are attained by DFPT. The mBJ gap is consistent with previously calculated HSE or B3LYP one, and has very better agreement with experiment than GGA one. The values of $d_{ij}$ are found to be comparable to or even superior than conventional piezoelectric materials such as $\alpha$-quartz, ZnO, AlN and GaN. These results show the possibility of employing piezoelectric effects in $\epsilon$-Ga$_2$O$_3$ for electronics and energy applications. Our works can stimulate further experimental works to study piezoelectric properties of $\epsilon$-Ga$_2$O$_3$.

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